

Infineon (G1 and G2) vs. Cree 6Amp and STMicroelectronics 10Amp SiC Schottky Diodes Teardown and Technology Analysis

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1. Product Identification

Manufacturer	Device ID	Date/lot code
Infineon Gen1	SDT06S60	6AA706
Infineon Gen2	SDT06S60C	6AB735
Cree	CSD06060 in TO263-2	B13506
ST	STPSC1006D in TO220	GK2CW VY

First and second generation devices from Infineon were studied. In this report they are referred to as Gen1 and Gen2 parts.

2. External Appearance and Principal Dimensions

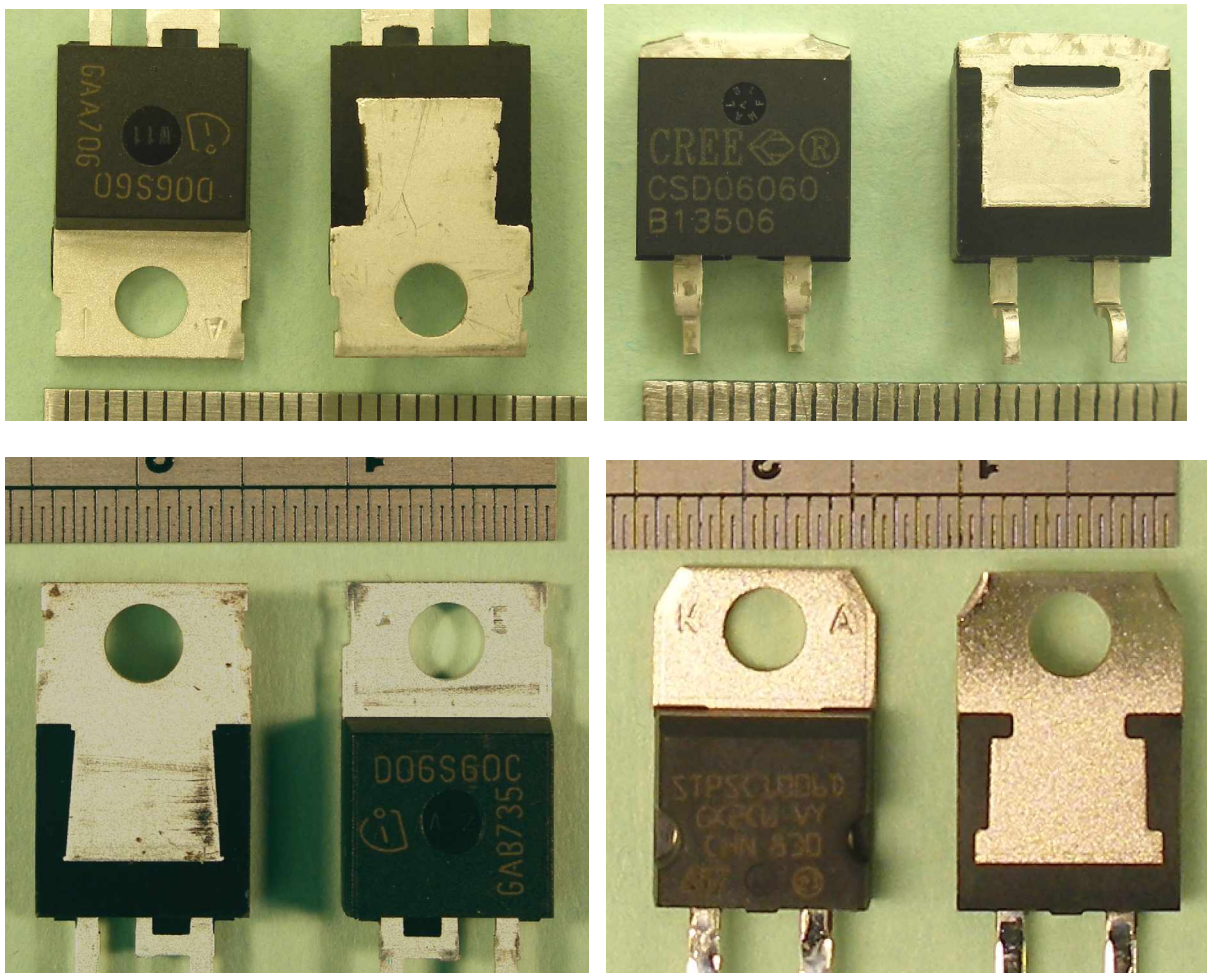


Figure 2.1 Infineon Gen1 device (top left), Cree device (top right), Infineon Gen2 (bottom left) and ST device (bottom right) subjected to teardown.

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